



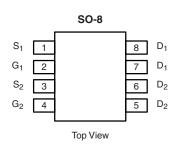
Dual N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
40	0.036 at V _{GS} = 10 V	5.7		
	0.059 at V _{GS} = 4.5 V	4.4		

FEATURES

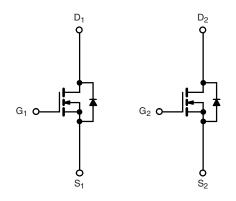
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4940DY-T1-E3 (Lead (Pb)-free)

Si4940DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	40		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Dunin Courset /T. 150 °CV8	T _A = 25 °C	- I _D	5.7	4.2	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		4.5	3.4	
Pulsed Drain Current		I _{DM}	30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	1.8	0.9	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.1	1.1	10/
	T _A = 70 °C		1.3	0.7	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifestore London La Austriania	t ≤ 10 s	R _{thJA}	50	60	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		90	110		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	28	34		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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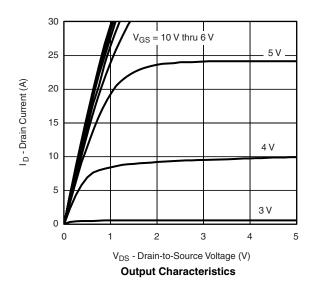
SPECIFICATIONS $T_J = 25$ °C Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = 32 V, V _{GS} = 0 V V _{DS} = 32 V, V _{GS} = 0 V, T _J = 55 °C			1	μΑ	
	I _{DSS}				5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Drain-Source On-State Resistance ^a	В	$V_{GS} = 10 \text{ V}, I_D = 5.7 \text{ A}$		0.03	0.036		
	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 4.4 A		0.048	0.059	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 5.7 \text{ A}$		12		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 1.8 A, V _{GS} = 0 V		0.8	1.1	V	
Dynamic ^b			•				
Total Gate Charge	Q_g			9.0	14		
Gate-Source Charge	Q_{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.7 \text{ A}$		1.8		nC	
Gate-Drain Charge	Q_{gd}			2.3			
Gate Resistance	R_g			1.0		Ω	
Turn-On Delay Time	t _{d(on)}			7	15		
Rise Time	t _r	V_{DD} = 20 V, R_L = 20 Ω		12	25		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		15	30	ns	
Fall Time	t _f			8	15		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.8 A, dI/dt = 100 A/μs		35	70		

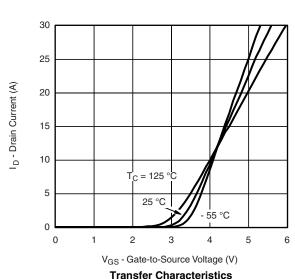
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C unless otherwise noted

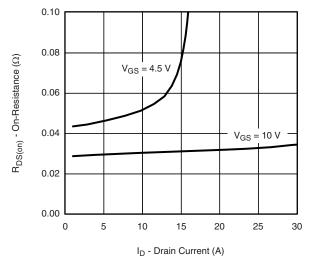




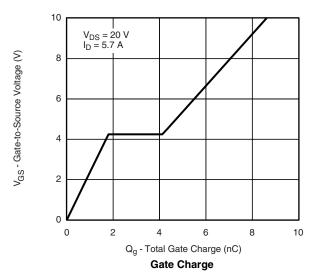


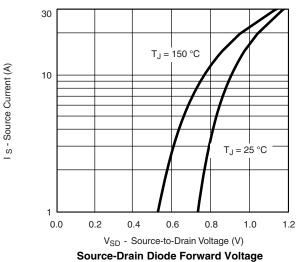


TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



On-Resistance vs. Drain Current





600
500
400
400
C_{iss}

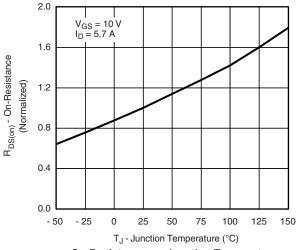
C_{oss}

100
C_{rss}

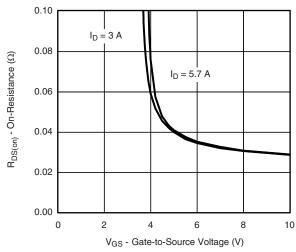
0
8
16
24
32
40

V_{DS} - Drain-to-Source Voltage (V) **Capacitance**





On-Resistance vs. Junction Temperature

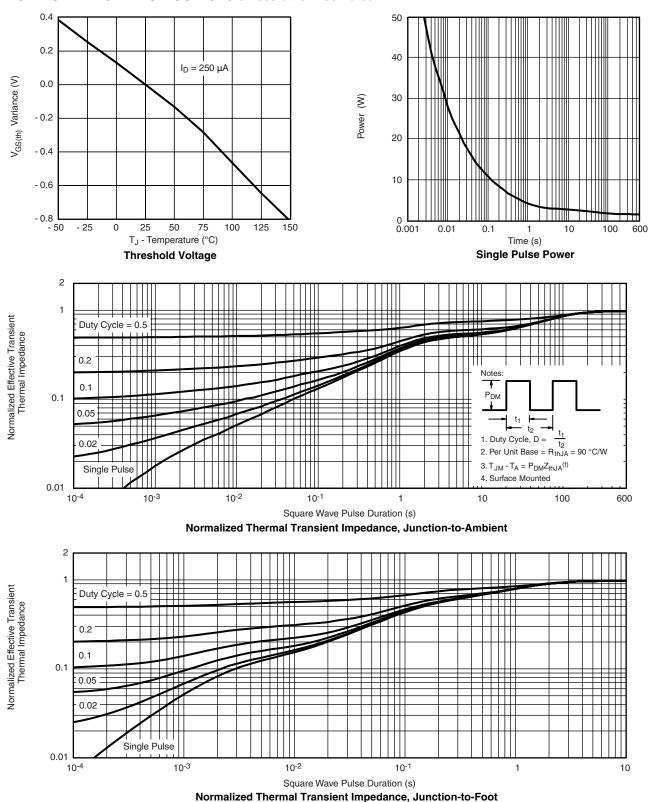


On-Resistance vs. Gate-to-Source Voltage

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TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



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